

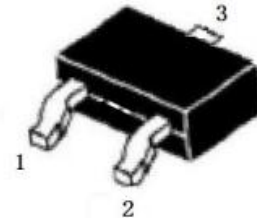
General Purpose Transistor NPN Silicon

◆ Features:

- ✧ Complementary to S9015
与 S9015 互补
- ✧ Excellent HFE linearity
优越的线性 HFE
- ✧ Power dissipation ($P_c = 0.2W$)
功耗 ($P_c = 0.2W$)

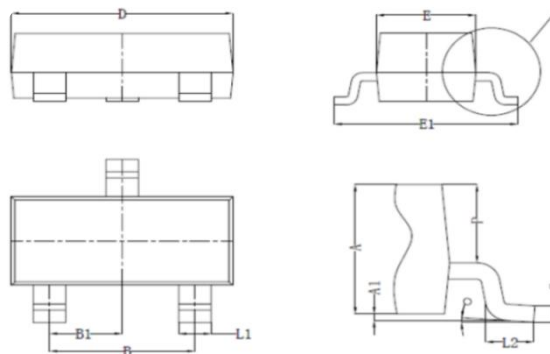
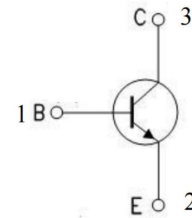


SOT-23



◆ Applications

- ✧ Small Signal Amplification
小信号放大
- ✧ Switching Circuits
开关电路
- ✧ RF Oscillators
射频振荡器
- ✧ Logic Level Conversion
逻辑电平转换



Symbol	Dim in mm		
	Min	Nor	Max
A	0.900	1.000	1.100
A1	0.000	0.050	0.100
L1	0.350	0.400	0.500
C	0.100	0.110	0.120
D	2.800	2.900	3.000
E	1.200	1.400	1.600
E1	2.250	2.400	2.550
B	1.800	1.900	2.000
B1	0.950TYP		
L2	0.200	0.350	0.450
P	0.550	0.575	0.600

◆ Absolute Maximum Ratings (Tc=25°C)

Symbol	Parameters	Ratings	Unit
VCBO	Collector-Base Voltage 集电极 - 基极电压	50	V
VCEO	Collector-Emitter Voltage 集电极 - 发射极电压	45	V
VEBO	Emitter-Base Voltage 发射极 - 基极电压	5	V
I _c	Collector Current-Continuous 集电极连续电流	100	mA
PC	Collector Power Dissipation 耗散功率	200	mW
T _j	Max.Operating junction temperature 最大结温	150	°C
T _{stg}	Storage Temperature 存储温度	-55 ~ +150	°C
R _{th(j-c)}	Thermal Resistance, Junction to Case 结到外壳的热阻	625	°C/W

◆ Electrical characteristics (Tc=25°C unless otherwise noted)

Symbol	Parameters	Min	Typ	Max	Units	Conditions
I_{CBO}	Collector Cutoff Current 集电极截止电流		--	0.1	μA	$V_{CB}=50V, I_B=0$
I_{EBO}	Emitter Cutoff Current 发射极截止电流		--	0.1	μA	$V_{EB}=5V, I_C=0$
BV_{CEO}	Collector Emitter Sustaining voltage(Note 1) 集电极发射极持续电压	45			V	$I_C=0.1mA, I_B=0$
$V_{CE(sat)}$	Collector Emitter Saturation Voltage(Note 1) 集电极发射极饱和电压			0.3	V	$I_C=100mA, I_B=5mA$
$V_{BE(sat)}$	Base-Emitter Saturation Voltage(Note 1) 基极发射极饱和电压			1.0	V	$I_C=100mA, I_B=5mA$
h_{FE}	DC Current Gain(Note 1) 直流电流增益	200	--	1000		$I_C=0.1A, V_{CE}=5V$
f_T	Current-Gain—Bandwidth 电流增益带宽	150	--	--	MHz	$V_{CE}=5V, I_C=10mA, f=30MHz$

Note 1: Pulse test: PW ≤ 300us , duty cycle ≤ 2%.